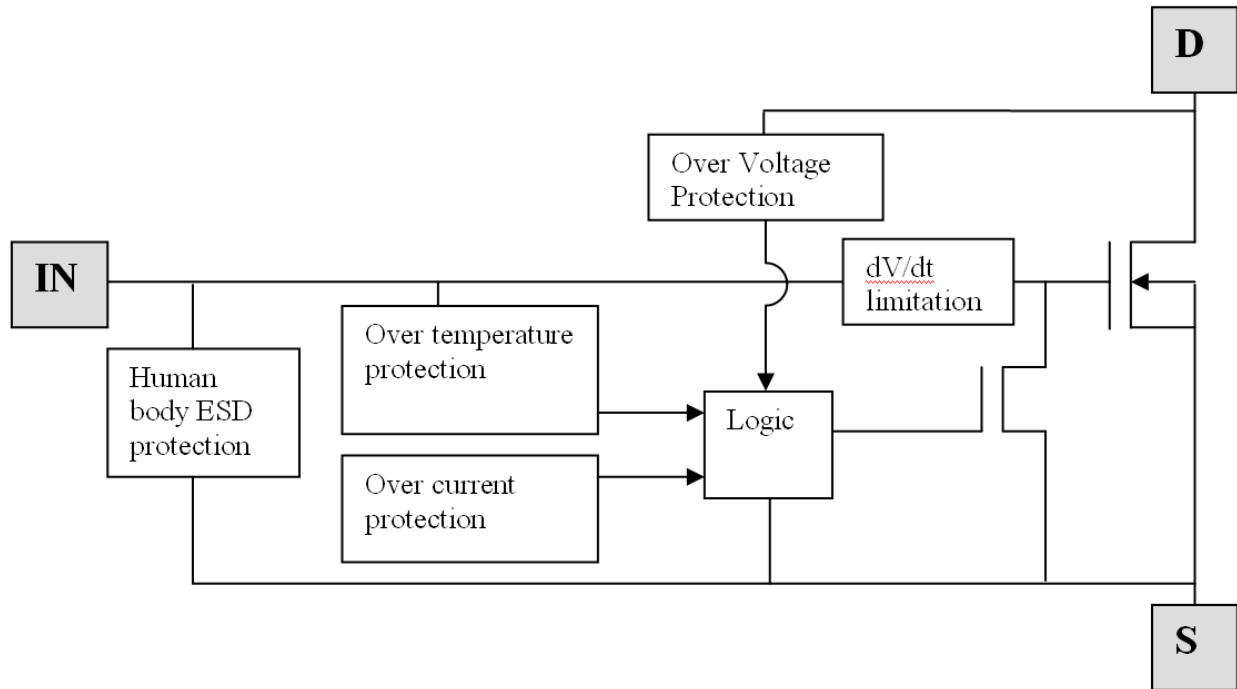


Functional Block Diagram



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Units
Continuous Drain-Source Voltage	V _{DS}	60	V
Drain-Source Voltage for Short Circuit Protection	V _{DS(SC)}	36	V
Continuous Input Voltage	V _{IN}	-0.5 to +6	V
Continuous Input Current @ -0.2V ≤ V _{IN} ≤ 6V	I _{IN}	No limit	mA
Continuous Input Current @ V _{IN} < -0.2V or V _{IN} > 6V	I _{IN}	I _{IN} ≤ 2	mA
Pulsed Drain Current @ V _{IN} = 3.3V	I _{DM}	2	A
Pulsed Drain Current @ V _{IN} = 5V	I _{DM}	2.5	A
Continuous Source Current (Body Diode) (Note 5)	I _S	1	A
Pulsed Source Current (Body Diode)	I _{SM}	5	A
Unclamped Single Pulse Inductive Energy, T _J = +25°C, I _D = 0.5A, V _{DD} = 24V	E _{AS}	120	mJ
Electrostatic Discharge (Human Body Model)	V _{HBM}	4,000	V
Charged Device Model	V _{CDM}	1,000	V

Thermal Resistance (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Power Dissipation at T _A = +25°C (Note 5)	P _D	1.28	W
Linear Derating Factor	P _D	10	mW/°C
Power Dissipation at T _A = +25°C (Note 6)	P _D	1.65	W
Linear Derating Factor	P _D	12.4	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	98	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	76	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	12	°C/W
Operating Temperature Range	T _J	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

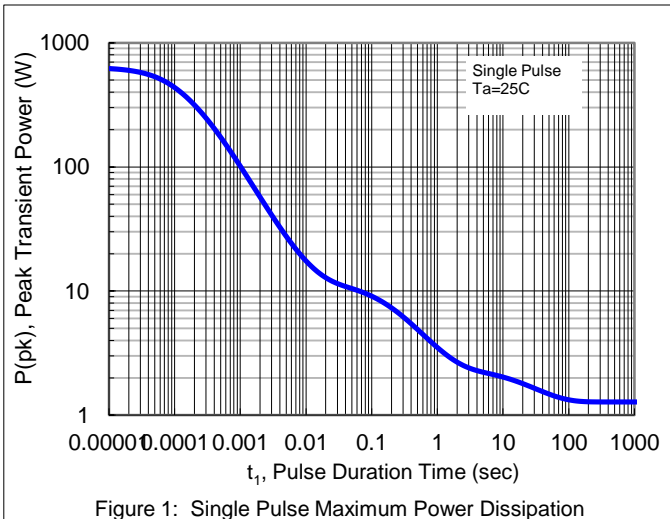
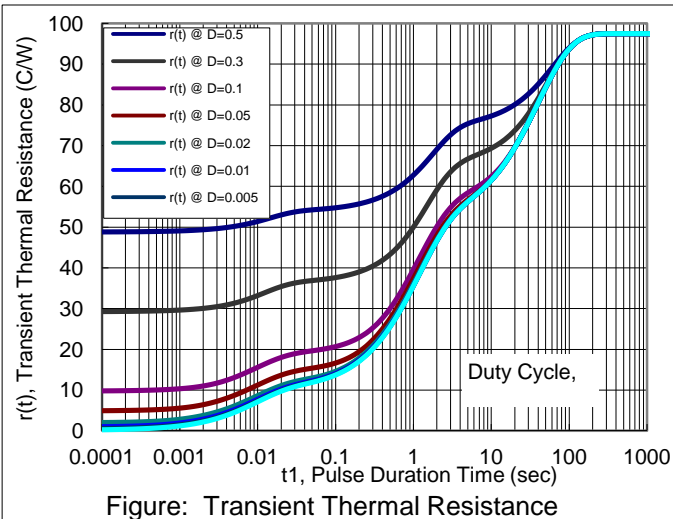
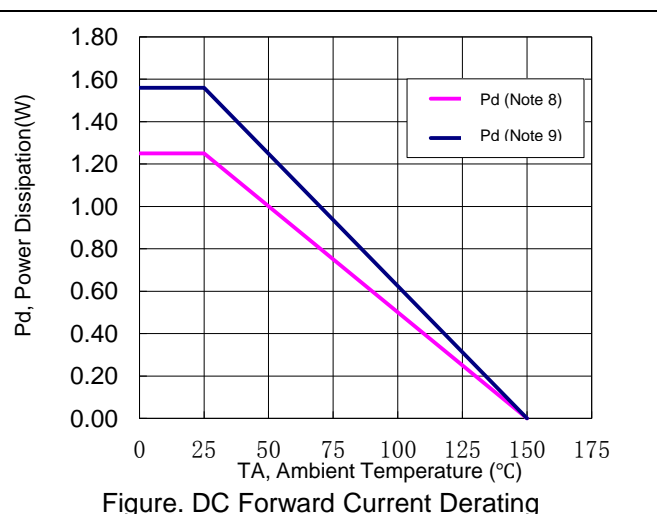
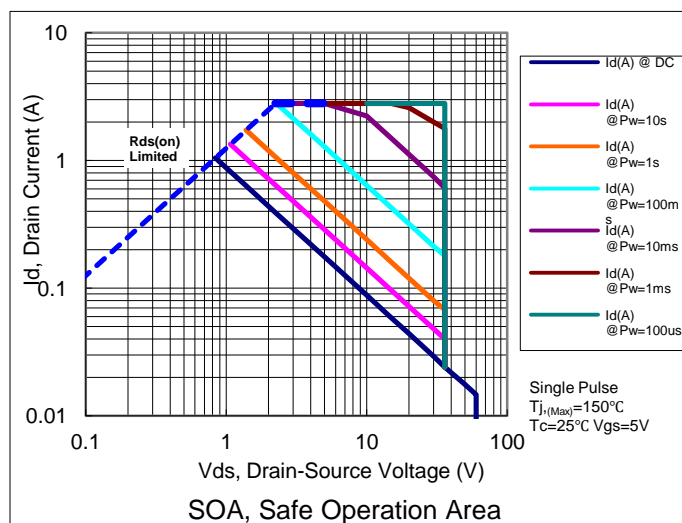
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Thermal resistance between junction and the mounting surfaces of drain and source pins.

Recommended Operating Conditions

The ZXMS6004N8 is optimized for use with μC operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V_{IN}	0	5.5	V
Ambient Temperature Range	T_A	-40	+125	$^{\circ}\text{C}$
High Level Input Voltage for MOSFET to be on	V_{IH}	3	5.5	V
Low Level Input Voltage for MOSFET to be off	V_{IL}	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	V_P	0	36	V

Thermal Characteristics



Note: 8. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
9. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Electrical Characteristics (@T_A = +25°C, unless otherwise stated.)

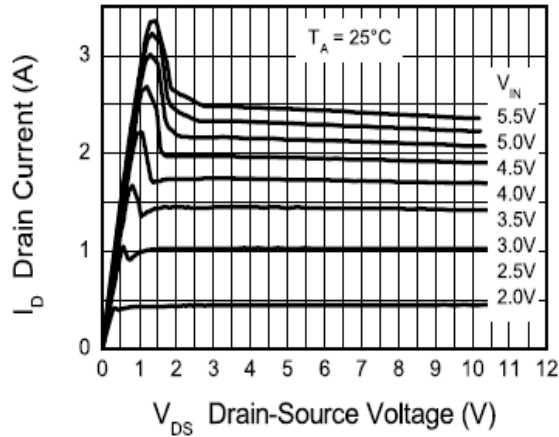
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	$V_{DS(AZ)}$	60	65	70	V	$I_D = 10\text{mA}$
Off State Drain Current	I_{DSS}	—	—	0.5	μA	$V_{DS} = 12\text{V}, V_{IN} = 0\text{V}$
		—	—	1		$V_{DS} = 36\text{V}, V_{IN} = 0\text{V}$
Input Threshold Voltage	$V_{IN(th)}$	0.7	1	1.5	V	$V_{DS} = V_{GS}, I_D = 1\text{mA}$
Input Current	I_{IN}	—	60	100	μA	$V_{IN} = +3\text{V}$
		—	120	200		$V_{IN} = +5\text{V}$
Input Current While Over-Temperature Active	—	—	—	400	μA	$V_{IN} = +5\text{V}$
Static Drain-Source On-State Resistance	$R_{DS(on)}$	—	400	600	$\text{m}\Omega$	$V_{IN} = +3\text{V}, I_D = 0.5\text{A}$
		—	350	500		$V_{IN} = +5\text{V}, I_D = 0.5\text{A}$
Continuous Drain Current (Note 5)	I_D	0.9	—	—	A	$V_{IN} = 3\text{V}; T_A = +25^\circ\text{C}$
		1.0	—	—		$V_{IN} = 5\text{V}; T_A = +25^\circ\text{C}$
Continuous Drain Current (Note 6)		1.2	—	—		$V_{IN} = 3\text{V}; T_A = +25^\circ\text{C}$
		1.3	—	—		$V_{IN} = 5\text{V}; T_A = +25^\circ\text{C}$
Current Limit (Note 10)	$I_{D(LIM)}$	0.7	1.7	—	A	$V_{IN} = +3\text{V}$
		1	2.2	—		$V_{IN} = +5\text{V}$
Dynamic Characteristics						
Turn On Delay Time	$t_{d(on)}$	—	5	—	μs	$V_{DD} = 12\text{V}, I_D = 0.5\text{A}, V_{GS} = 5\text{V}$
Rise Time	t_r	—	10	—		
Turn Off Delay Time	$t_{d(off)}$	—	45	—		
Fall Time	t_f	—	15	—		
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 11)	T_{JT}	150	+175	—	$^\circ\text{C}$	—
Thermal Hysteresis (Note 11)	ΔT_{JT}	—	+10	—	$^\circ\text{C}$	—

Notes:

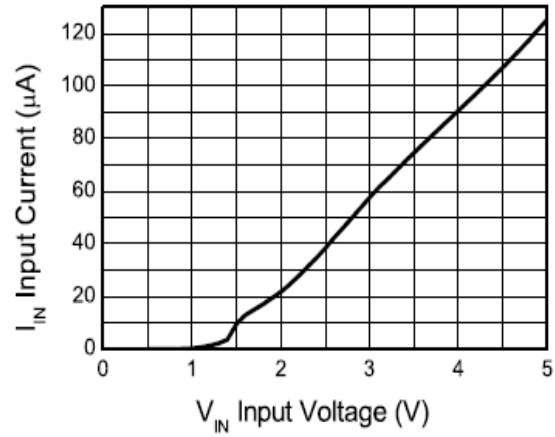
10. The drain current is restricted only when the device is in saturation (see graph 'typical output characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

11. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

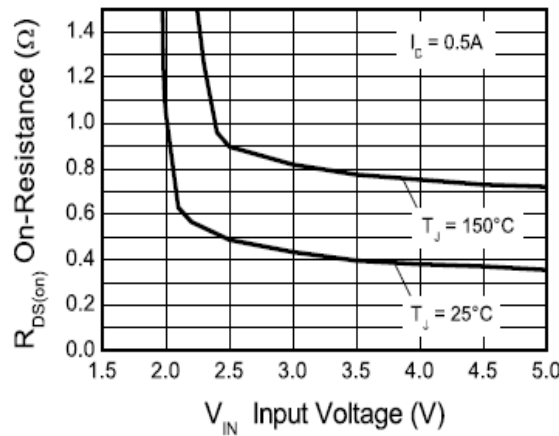
Typical Characteristics



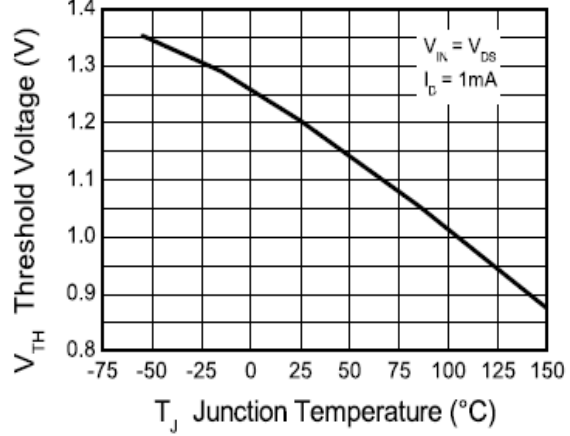
Typical Output Characteristic



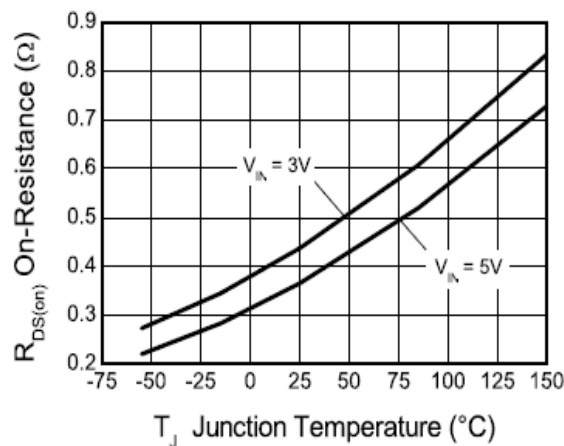
Input Current vs Input Voltage



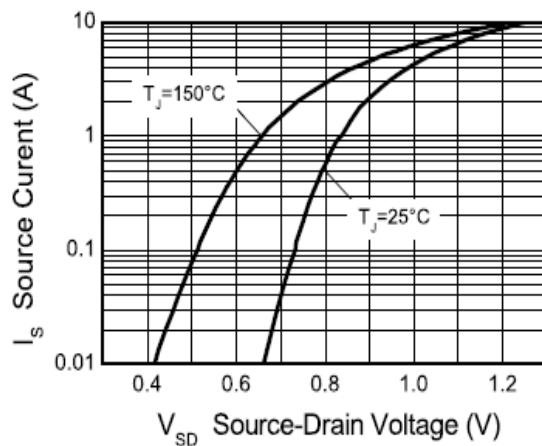
On-Resistance vs Input Voltage



Threshold Voltage vs Temperature

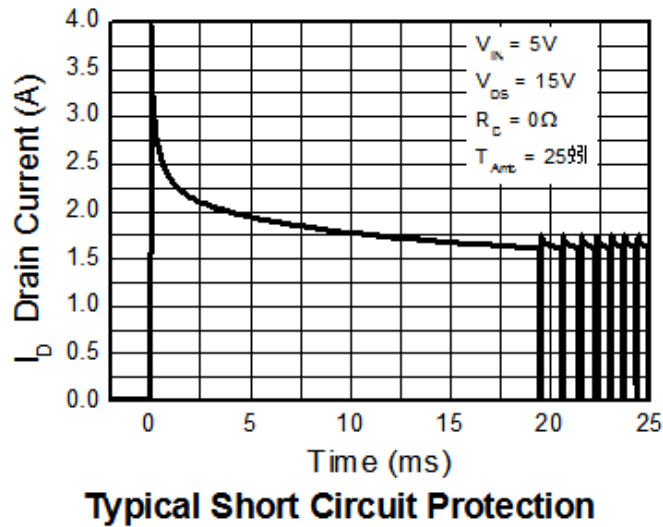
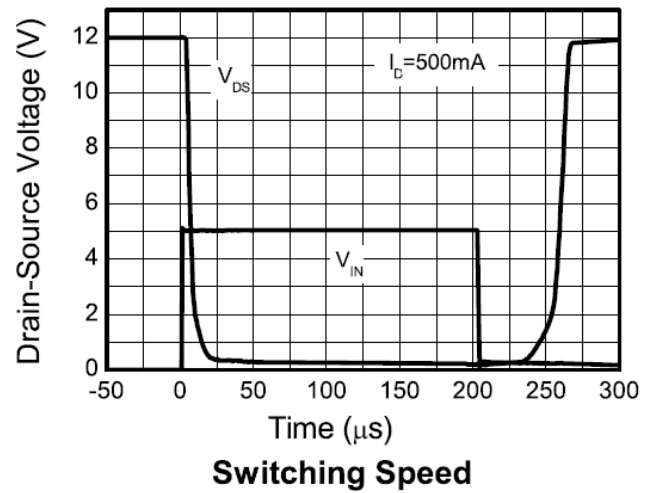
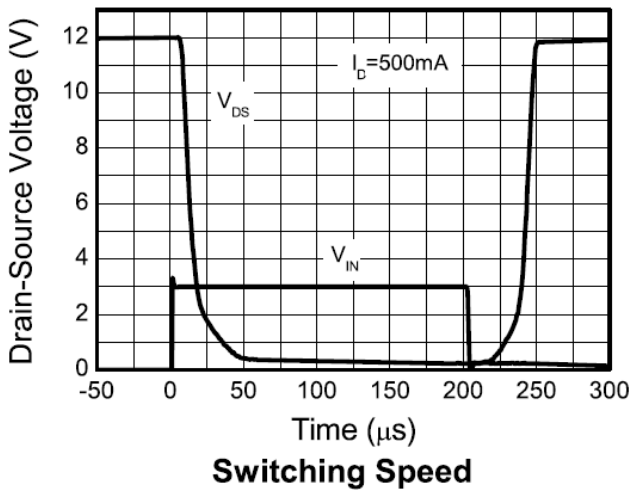


On-Resistance vs Temperature



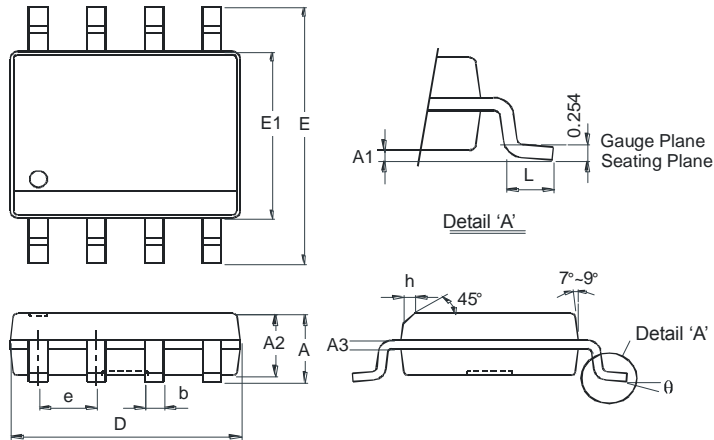
Reverse Diode Characteristic

Typical Characteristics (continued)



Package Outline Dimensions

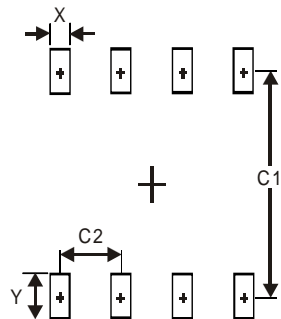
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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